Vishay Semiconductors

# 650 V Gen 4 Power Silicon Carbide Schottky Diode, 10 A



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## LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS									
I <sub>F(AV)</sub> 10 A									
V <sub>R</sub>	650 V								
V <sub>F</sub> at I <sub>F</sub> at 25 °C, typ.	1.3 V								
T <sub>J</sub> max.	175 °C								
I <sub>R</sub> at V <sub>R</sub> at 175 °C	50 µA								
$Q_{C} (V_{R} = 400 V)$	27 nC								
Package	TO-220AC 2L								
Circuit configuration	Single								

## **FEATURES**

- Positive V<sub>F</sub> temperature coefficient for easy paralleling RoHS
- Virtually no recovery tail and no switching losses COMPLIANT
- Temperature invariant switching behavior HALOGEN FREE
- 175 °C maximum operating junction temperature
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Solder bath temperature 275 °C maximum, 10 s per JESD 22-B106
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

## **DESCRIPTION / APPLICATIONS**

Wide band gap SiC based 650 V Schottky diode, designed for high performance and ruggedness.

Optimized for extreme high-speed hard switching across a wide temperature range. This SiC diode is ideal for demanding applications such as high efficiency PFC diodes and ultra-high frequency output rectifiers in AC/DC and DC/DC converters.

## **MECHANICAL DATA**

Case: TO-220AC 2L

Molding compound meets UL 94 V-0 flammability rating

Base P/N HM3 - halogen-free, RoHS-compliant, and AEC-Q101 qualified

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Mounting torque: 10 in-lbs maximum

<b>MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Peak repetitive reverse voltage	V <sub>RRM</sub>		650	V					
Continuous forward current	I <sub>F</sub> <sup>(1)</sup>	T <sub>C</sub> = 145 °C (DC)	10	А					
Continuous forward current	I <sub>F</sub> <sup>(2)</sup>	T <sub>C</sub> = 138 °C (DC)	10	А					
DC blocking voltage	V <sub>DC</sub>		650	V					
Repetitive peak forward current	tak forward current $I_{FRM}$ $T_C = 25 ^{\circ}C$ , f = 50 Hz, square wave, DC = 25 $\%$		42						
Non repetitive peak ferward over a surrent	I <sub>FSM</sub>	$T_{C} = 25 \text{ °C}, t_{p} = 10 \text{ ms}, \text{ half sine wave}$	60	А					
Non-repetitive peak forward surge current		$T_{C}$ = 110 °C, $t_{p}$ = 10 ms, half sine wave	48	]					
	P <sub>tot</sub> <sup>(1)</sup>	T <sub>C</sub> = 25 °C	79	W					
Dewer discipation	Ptot '''	T <sub>C</sub> = 110 °C	34	vv					
Power dissipation	P <sub>tot</sub> <sup>(2)</sup>	T <sub>C</sub> = 25 °C	62.5						
	rtot (−)	T <sub>C</sub> = 110 °C	27						
124	∫i <sup>2</sup> dt	T <sub>C</sub> = 25 °C	18	A2-					
l <sup>2</sup> t value	ji dt	T <sub>C</sub> = 110 °C	11.5	A <sup>2</sup> s					
Operating junction and storage temperatures	T <sub>J</sub> <sup>(2)</sup> , T <sub>Stg</sub>		-55 to +175	°C					

#### Notes

(1) Based on typical R<sub>th</sub>

<sup>(2)</sup> Based on maximum R<sub>th</sub>

 $^{(3)}$  The heat generated must be less than the thermal conductivity from junction-to-ambient:  $dP_D/dT_1 < 1/R_{0.IA}$ 

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## **Vishay Semiconductors**

<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J$ = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Forward voltage		I <sub>F</sub> = 10 A	-	1.3	1.5	v			
	V <sub>F</sub>	I <sub>F</sub> = 10 A, T <sub>J</sub> = 150 °C	-	1.45	1.75				
		I <sub>F</sub> = 10 A, T <sub>J</sub> = 175 °C	-	1.55	-				
	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	2	80	μA			
Reverse leakage current		$V_R = V_R$ rated, $T_J = 150 \ ^\circ C$	-	23	160				
		$V_{R} = V_{R}$ rated, $T_{J} = 175 \text{ °C}$	-	50	-				
Total capacitance	С	V <sub>R</sub> = 1 V, f = 1 MHz	-	440	-	pF			
Total capacitance		V <sub>R</sub> = 400 V, f = 1 MHz	-	38	-	рг			
Total capacitive charge	Q <sub>C</sub>	V <sub>R</sub> = 400 V, f = 1 MHz	-	27	-	nC			

<b>THERMAL AND MECHANICAL SPECIFICATIONS</b> (T <sub>A</sub> = 25 °C unless otherwise specified)										
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNIT									
Thermal resistance, junction to case	R <sub>thJC</sub>		-	1.9	2.4	°C/W				
Marking device		4C10ET07T								

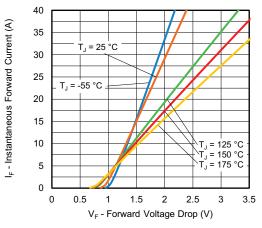


Fig. 1 - Typical Forward Voltage Drop Characteristics

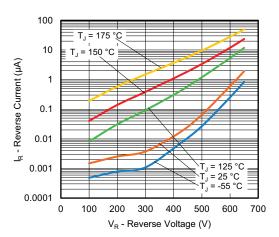


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

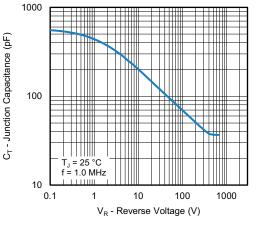


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

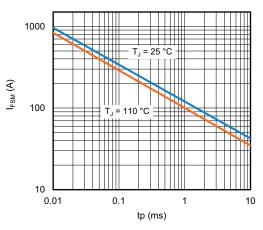
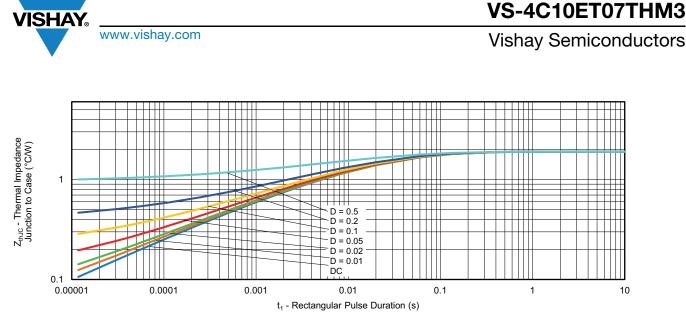


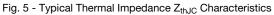
Fig. 4 - Non-Repetitive Peak Forward Surge Current vs. Pulse Duration (Square Wave)

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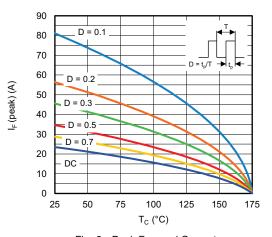


Fig. 6 - Peak Forward Current vs. Maximum Allowable Case Temperature

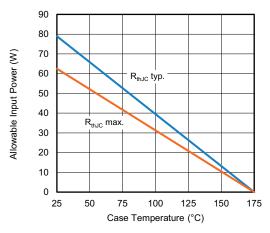


Fig. 7 - Forward Power Loss Characteristics

10 8 Capacitive Energy (µJ) 6 4 T\_ = 25 °C 2 C V dV  $E_{\ell} =$ 0 100 200 300 400 600 700 0 500 Reverse Voltage (V)

Fig. 8 - Typical Capacitive Energy vs. Reverse Voltage

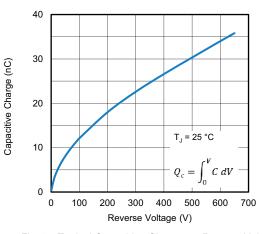


Fig. 9 - Typical Capacitive Charge vs. Reverse Voltage

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# VS-4C10ET07THM3

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## **ORDERING INFORMATION TABLE**

Device code	VS-	4C	10	E	т	07	т	н	МЗ
		2	3	4	5	6	7	8	9
	1 -   2 -   3 -   3 -   4 -   5 -   6 -   7 -   8 -	- 4C - Cur - E = - T = - Vol - T =	= SiC o rrent rati single o TO-220 tage rati true 2 p	diode, go ing (10 = diode ) packag ing: (07 bin	ge = 650 V	n 4			
	9	- Env	AEC-Q vironmer = halog	ntal digi	t:	complia	nt, and	terminat	tion lead

ORDERING INFORMATION										
PREFERRED P/N	UNIT WEIGHT	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-4C10ET07THM3	2 g	50 per tube	Antistatic plastic tube							

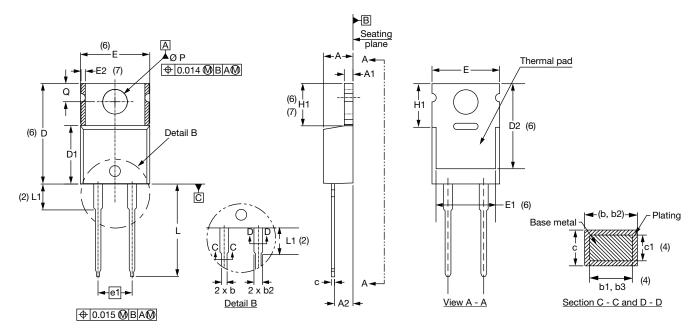
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96069
Part marking information	www.vishay.com/doc?95391



Vishay Semiconductors

TO-220AC 2L

## **DIMENSIONS** in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES	STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183		E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055		E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115		e1	4.88	5.28	0.192	0.208	
b	0.69	1.01	0.027	0.040		H1	5.84	6.86	0.230	0.270	6, 7
b1	0.38	0.97	0.015	0.038	4	L	13.52	14.02	0.532	0.552	
b2	1.20	1.73	0.047	0.068		L1	3.32	3.82	0.131	0.150	2
b3	1.14	1.73	0.045	0.068	4	ØΡ	3.54	3.73	0.139	0.147	
с	0.36	0.61	0.014	0.024		Q	2.60	3.00	0.102	0.118	
c1	0.36	0.56	0.014	0.022	4						
D	14.85	15.25	0.585	0.600	3						
D1	8.38	9.02	0.330	0.355							
D2	11.68	12.88	0.460	0.507	6						
E	10.11	10.51	0.398	0.414	3, 6						

Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

<sup>(5)</sup> Controlling dimension: inches

<sup>(6)</sup> Thermal pad contour optional within dimensions E, H1, D2 and E1

<sup>(7)</sup> Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed

<sup>(8)</sup> Outline conforms to JEDEC<sup>®</sup> TO-220, except D2, where JEDEC<sup>®</sup> minimum is 0.480"

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